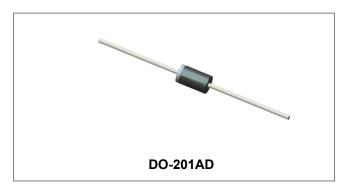






SB10150 SCHOTTKY RECTIFIER



Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	150	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _A =75°C, rectangular wave form	10	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse, T _C =25°C	200	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	V _{F1} @ 10A, Pulse, T _J = 25 °C		1.05	V
	V _{F2}	@ 10A, Pulse, T _J = 125 °C	0.70	0.90	V
Reverse Current*	I _{R1}	@V _R = Rated V _R , Pulse, T _J = 25 °C	0.0004	1	mA
	I _{R2}	@V _R = Rated V _R , Pulse, T _J = 125 °C	0.2	7.0	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 ^{\circ}C, f_{SIG} = 1MHz$	180	300	pF

^{*} Pulse width < 300 µs, duty cycle < 2%

- China Germany Korea Singapore United States
 - http://www.smc-diodes.com
 sales@ smc-diodes.com



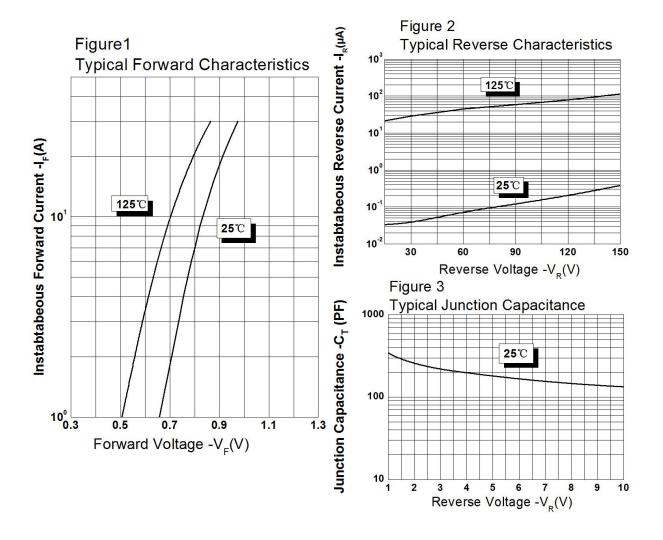




Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Ambient	$R_{ heta JA}$	DC operation	10	°C/W
Approximate Weight	wt	-	1.02	g

Ratings and Characteristics Curves

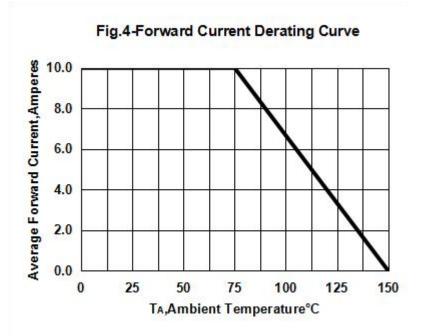


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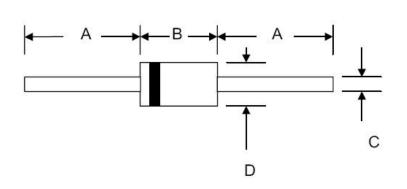








Mechanical Dimensions DO-201AD



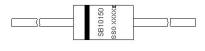
CYMPOL	Millimeters		Inches		
SYMBOL	Min.	Max.	Min.	Max.	
А	25.4	-	1.000	-	
В	8.50	9.50	0.335	0.374	
С	1.2	1.3	0.048	0.052	
D	5.0	5.6	0.197	0.220	

Ordering Information

Device	Package	Shipping	
SB10150	DO-201AD	1250nos / tono	
SB10130	(Pb-Free)	1250pcs / tape	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXXX is YYWWL

SB10150 SSG YY

= Part Name = SSG = Year

WW L = Week = Lot Number

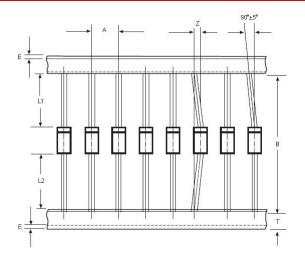
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Carrier Tape Specification DO-201AD



SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
Α	9.50	10.50	
В	50.9	53.9	
Z	-	1.20	
Т	5.60	6.40	
E	-	0.80	
IL1-L2I	-	1.0	

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